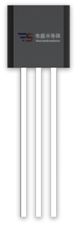
2SC536 TRANSISTOR (NPN)



1.EMITTER
2.COLLECTOR
3.BASE

FEATURES

- General Purpose Amplifier Transistor

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SC536	TO-92	Bulk	1000pcs/Bag
2SC536-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	0.1	A
P_C	Collector Power Dissipation	0.4	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	312	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

T_a=25 ℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 0.1mA,I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=0.1mA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=35V,I_E=0			1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V,I_C=0			1	μA
DC current gain	h_{FE}	V_{CE}=6V, I_C=1mA	60		960	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=50mA,I_B=5mA			0.5	V
Collector output capacitance	C_{ob}	V_{CB}=6V, f=1MHz		3.5		pF
Transition frequency	f_T	V_{CE}=6V,I_C=1mA		100		MHz

CLASSIFICATION OF h_{FE}

RANK	D	E	F	G	H
RANGE	60-120	100-200	160-320	280-560	480-960